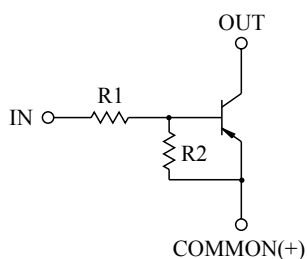


SWITCHING APPLICATION.  
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

### FEATURES

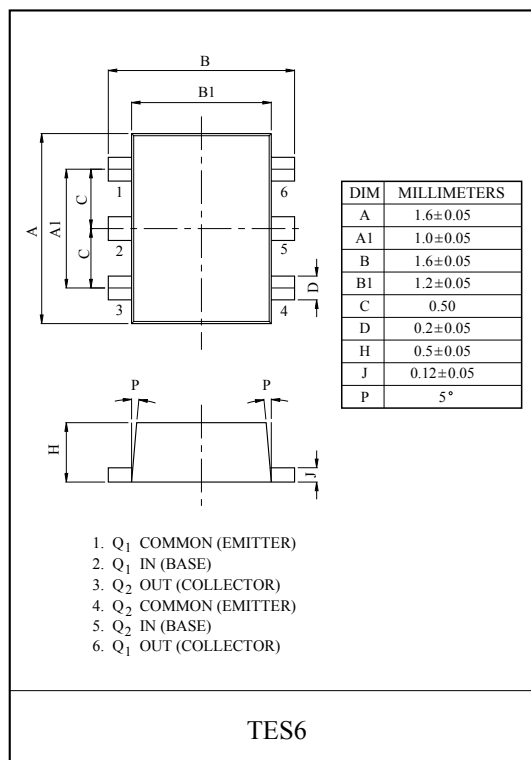
- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- High Packing Density.

### EQUIVALENT CIRCUIT

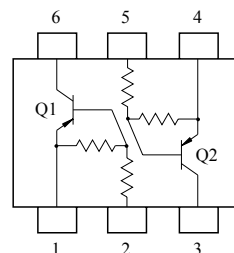


### BIAS RESISTOR VALUES

TYPE NO.	R1(k $\Omega$ )	R2(k $\Omega$ )
KRA757E	10	47
KRA758E	22	47
KRA759E	47	22



### EQUIVALENT CIRCUIT (TOP VIEW)



### MAXIMUM RATING (Ta=25℃)

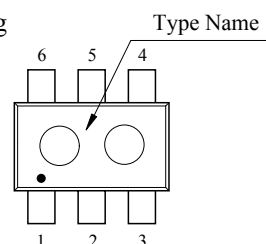
CHARACTERISTIC		SYMBOL	RATING	UNIT
Output Voltage	KRA757E ~ 759E	V <sub>O</sub>	-50	V
Input Voltage	KRA757E	V <sub>I</sub>	-30, 6	V
	KRA758E		-40, 7	
	KRA759E		-40, 15	
Output Current	KRA757E ~ 759E	I <sub>O</sub>	-100	mA
Power Dissipation		P <sub>D</sub> *	200	mW
Junction Temperature		T <sub>j</sub>	150	℃
Storage Temperature Range		T <sub>stg</sub>	-55 ~ 150	℃

\* Total Rating.

### MARK SPEC

TYPE	KRA757E	KRA758E	KRA759E
MARK	PH	PI	PJ

### Marking



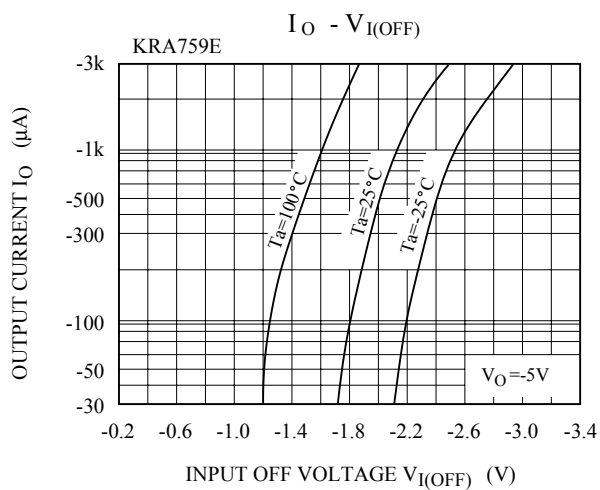
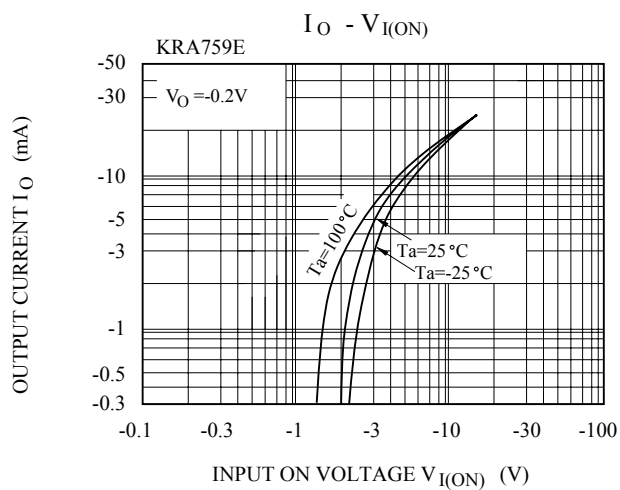
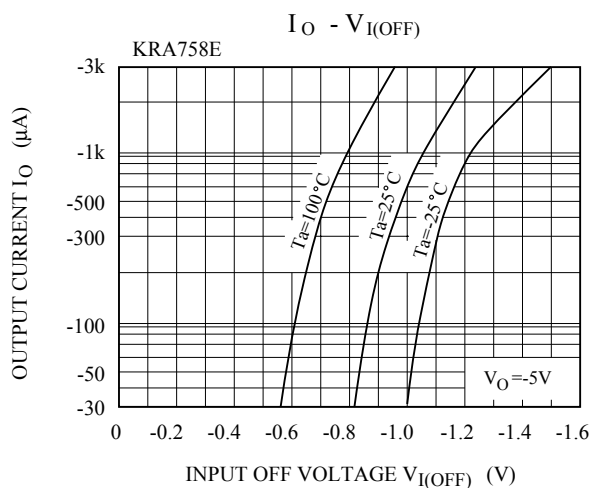
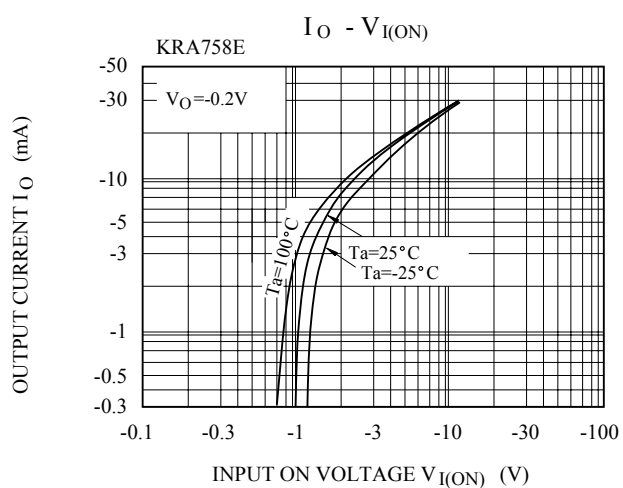
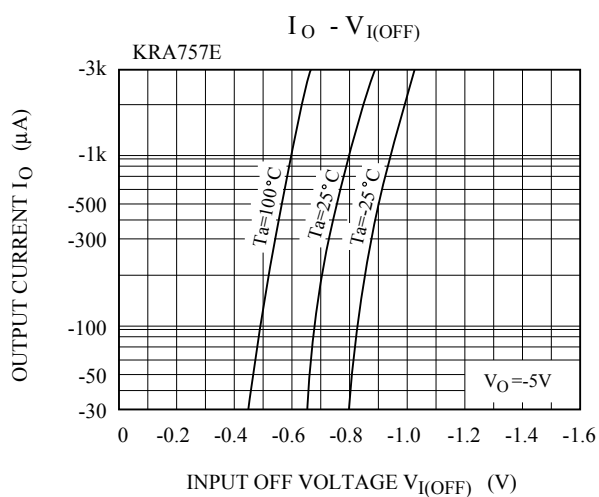
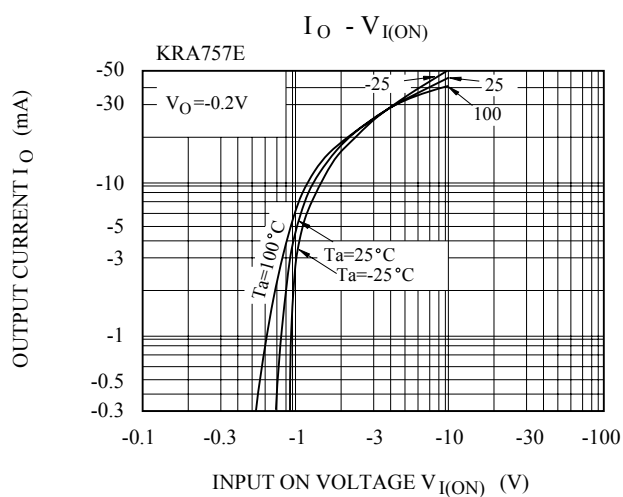
# KRA757E~KRA759E

## ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Output Cut-off Current		KRA757E ~ 759E	I <sub>O(OFF)</sub>	V <sub>O</sub> =-50V, V <sub>I</sub> =0	-	-	-500	nA	
DC Current Gain	KRA757E	G <sub>I</sub>	V <sub>O</sub> =-5V, I <sub>O</sub> =-10mA	80	150	-			
	KRA758E			80	150	-			
	KRA759E			70	140	-			
Output Voltage		KRA757E ~ 759E	V <sub>O(ON)</sub>	I <sub>O</sub> =-10mA, I <sub>I</sub> =-0.5mA	-	-0.1	-0.3	V	
Input Voltage (ON)	KRA757E	V <sub>I(ON)</sub>	V <sub>O</sub> =-0.2V, I <sub>O</sub> =-5mA	-	-1.2	-1.8	V		
	KRA758E			-	-1.8	-2.6			
	KRA759E			-	-3.0	-5.8			
Input Votlage (OFF)	KRA757E	V <sub>I(OFF)</sub>	V <sub>O</sub> =-5V, I <sub>O</sub> =-0.1mA	-0.5	-0.75	-	V		
	KRA758E			-0.6	-0.88	-			
	KRA759E			-1.5	-1.82	-			
Transition Frequency		KRA757E ~ 759E	f <sub>T</sub> *	V <sub>O</sub> =-10V, I <sub>O</sub> =-5mA	-	200	-	MHz	
Input Current		KRA757E	I <sub>I</sub>	V <sub>I</sub> =-5V	-	-	-0.88	mA	
		KRA758E			-	-	-0.36		
		KRA759E			-	-	-0.16		
Switching Time	Rise Time	KRA757E	t <sub>r</sub>	V <sub>O</sub> =-5V, V <sub>IN</sub> =-5V R <sub>L</sub> =1kΩ	-	0.07	-	μS	
		KRA758E			-	0.20	-		
		KRA759E			-	0.38	-		
	Storage Time	KRA757E			t <sub>stg</sub>	-	1.1		-
		KRA758E				-	1.3		-
		KRA759E				-	0.7		-
	Fall Time	KRA757E			t <sub>f</sub>	-	0.35		-
		KRA758E				-	0.4		-
		KRA759E				-	0.48		-

Note : \* Characteristic of Transistor Only.

# KRA757E~KRA759E



# KRA757E~KRA759E

